NSS12200WT1G

Low $V_{CE(sat)}$ Transistor, PNP, 12 V, 2.0 A, SOT-363 Package

ON Semiconductor's e²PowerEdge family of low $V_{CE(sat)}$ transistors are miniature surface mount devices featuring ultra low saturation voltage ($V_{CE(sat)}$) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical application are DC−DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e²PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

Features

- High Current Capability (3 A)
- High Power Handling (Up to 650 mW)
- Low $V_{CE(s)}$ (170 mV Typical @ 1 A)
- Small Size
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Benefits

- High Specific Current and Power Capability Reduces Required PCB Area
- Reduced Parasitic Losses Increases Battery Life

MAXIMUM RATINGS (T_A = 25°C)

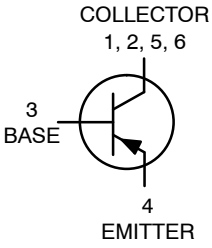
Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V_{CEO}	−12	Vdc
Collector-Base Voltage	V_{CBO}	−12	Vdc
Emitter-Base Voltage	V_{EBO}	−5.0	Vdc
Collector Current − Continuous − Peak	I_C I_{CM}	−2.0 −3.0	Adc
Electrostatic Discharge	ESD	HBM Class 3 MM Class C	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

ON Semiconductor®

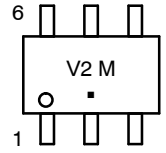
http://onsemi.com

12 VOLTS
2.0 AMPS
PNP LOW $V_{CE(sat)}$ TRANSISTOR
EQUIVALENT $R_{DS(on)}$ 163 mΩ



SC−88/SOT−363
CASE 419B
STYLE 20

DEVICE MARKING



V2 = Specific Device Code
M = Date Code
▪ = Pb−Free Package

ORDERING INFORMATION

Device	Package	Shipping†
NSS12200WT1G	SOT−363 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation T_A = 25°C Derate above 25°C	P_D (Note 1)	450 3.6	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$ (Note 1)	275	°C/W
Total Device Dissipation T_A = 25°C Derate above 25°C	P_D (Note 2)	650 5.2	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$ (Note 2)	192	°C/W
Thermal Resistance, Junction−to−Lead 6	$R_{\theta JL}$	105	°C/W
Total Device Dissipation (Single Pulse < 10 sec.)	P_D Single	1.4	W
Junction and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector − Emitter Breakdown Voltage, (I_C = −10 mAdc, I_B = 0)	$V_{(BR)CEO}$	−12	−15	−	Vdc
Collector − Base Breakdown Voltage, (I_C = −0.1 mAdc, I_E = 0)	$V_{(BR)CBO}$	−12	−25	−	Vdc
Emitter − Base Breakdown Voltage, (I_E = −0.1 mAdc, I_C = 0)	$V_{(BR)EBO}$	−5.0	−7.0	−	Vdc
Collector Cutoff Current, (V_{CB} = −12 Vdc, I_E = 0)	I_{CBO}	−	−0.02	−0.1	μAdc
Collector−Emitter Cutoff Current, (V_{CES} = −12 Vdc, I_E = 0)	I_{CES}	−	−0.03	−0.1	μAdc
Emitter Cutoff Current, (V_{EB} = −5.0 Vdc, I_E = 0)	I_{EBO}	−	−0.03	−0.1	μAdc
ON CHARACTERISTICS					
DC Current Gain (Note 3) (I_C = −0.5 A, V_{CE} = −1.5 V) (I_C = −0.8 A, V_{CE} = −1.5 V) (I_C = −1.0 A, V_{CE} = −1.5 V)	h_{FE}	 100 100 100	 180 165 160	 − 300 −	
Collector − Emitter Saturation Voltage (Note 3) (I_C = −0.5 A, I_B = −10 mA) (I_C = −0.8 A, I_B = −16 mA) (I_C = −1.0 A, I_B = −20 mA)	$V_{CE(sat)}$	 − − −	 −0.10 −0.14 −0.17	 −0.160 −0.235 −0.290	V
Base − Emitter Saturation Voltage (Note 3) (I_C = −1.0 A, I_B = −20 mA)	$V_{BE(sat)}$	−	−0.84	−0.95	V
Base − Emitter Turn−on Voltage (Note 3) (I_C = −1.0 A, V_{CE} = −1.5 V)	$V_{BE(on)}$	−	−0.81	−0.95	V
Cutoff Frequency (I_C = −100 mA, V_{CE} = −5.0 V, f = 100 MHz)	f_T	−	100	−	MHz
Output Capacitance (V_{CB} = −1.5 V, f = 1.0 MHz)	C_{obo}	−	50	65	pF

1. FR−4, Minimum Pad, 1 oz Coverage.
2. FR−4, 1″ Pad, 1 oz Coverage.
3. Pulsed Condition: Pulse Width < 300 μsec, Duty Cycle < 2%.

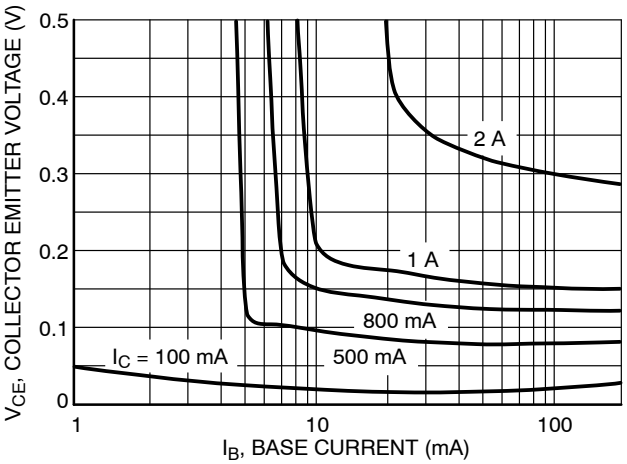


Figure 1. Collector Emitter Voltage vs. Base Current

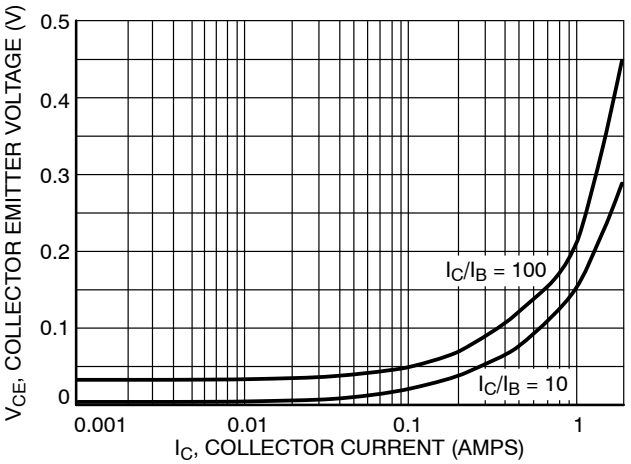


Figure 2. Collector Emitter Voltage vs. Collector Current

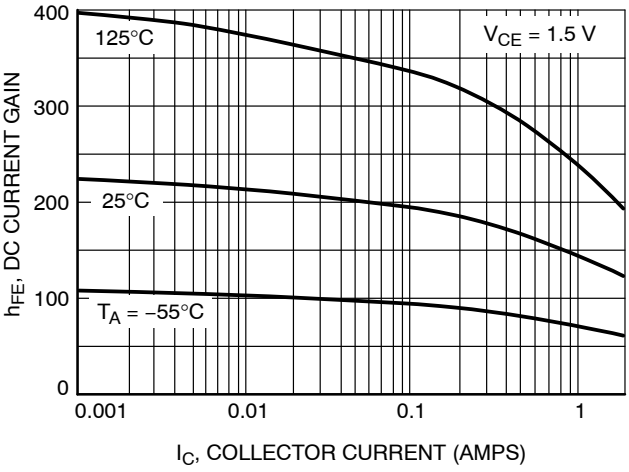


Figure 3. DC Current Gain vs. Collector Current

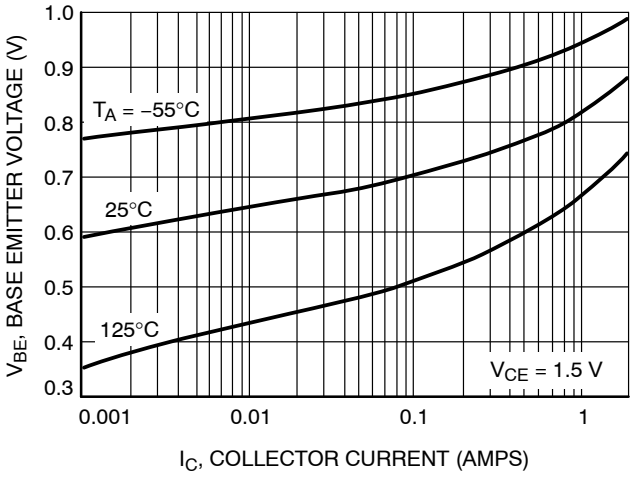


Figure 4. Base Emitter Voltage vs. Collector Current

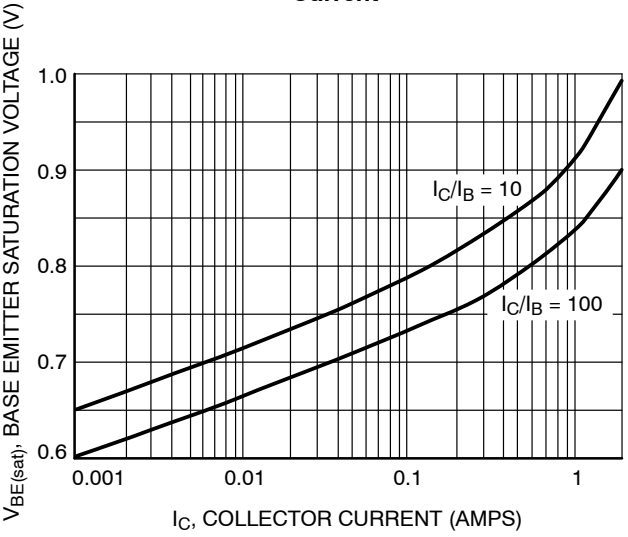


Figure 5. Base Emitter Saturation Voltage vs. Base Current

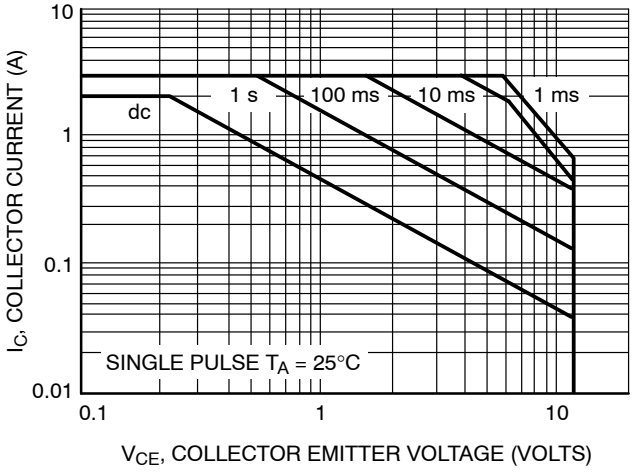


Figure 6. Safe Operating Area

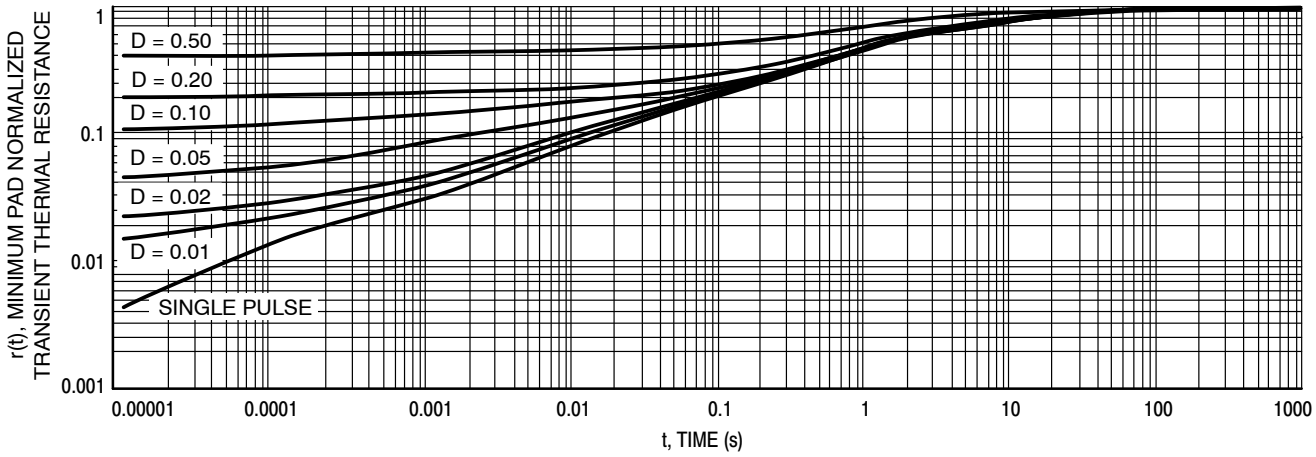
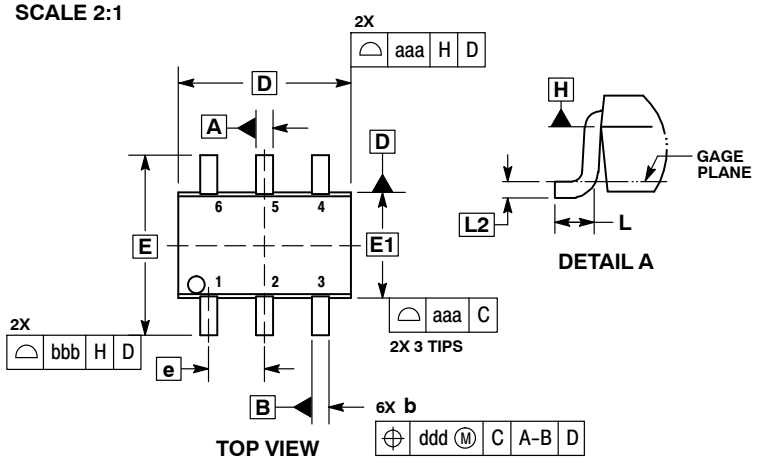


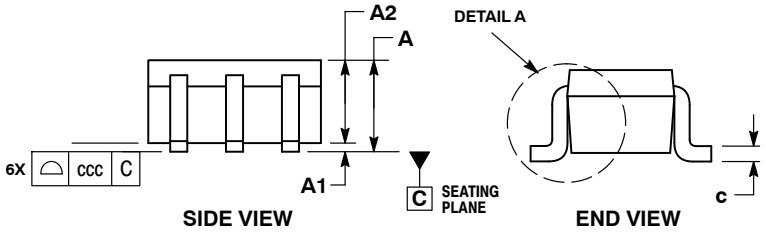
Figure 7. Normalized Thermal Response

SC−88/SC70−6/SOT−363
CASE 419B−02
ISSUE Y

DATE 11 DEC 2012

1
SCALE 2:1

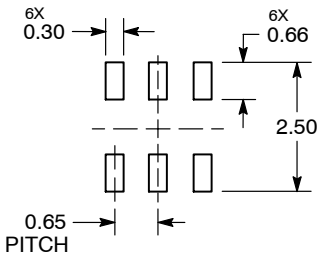




NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

	MILLIMETERS			INCHES		
DIM	**MIN**	**NOM**	**MAX**	**MIN**	**NOM**	**MAX**
A	−−−	−−−	1.10	−−−	−−−	0.043
A1	0.00	−−−	0.10	0.000	−−−	0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
C	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			0.006 BSC		
aaa	0.15			0.006		
bbb	0.30			0.012		
ccc	0.10			0.004		
ddd	0.10			0.004		

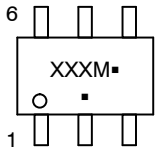
RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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CASE 419B−02
ISSUE Y

DATE 11 DEC 2012

STYLE 1:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

STYLE 2:
CANCELLED

STYLE 3:
CANCELLED

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. COLLECTOR
4. EMITTER
5. BASE
6. ANODE

STYLE 5:
PIN 1. ANODE
2. ANODE
3. COLLECTOR
4. EMITTER
5. BASE
6. CATHODE

STYLE 6:
PIN 1. ANODE 2
2. N/C
3. CATHODE 1
4. ANODE 1
5. N/C
6. CATHODE 2

STYLE 7:
PIN 1. SOURCE 2
2. DRAIN 2
3. GATE 1
4. SOURCE 1
5. DRAIN 1
6. GATE 2

STYLE 8:
CANCELLED

STYLE 9:
PIN 1. EMITTER 2
2. EMITTER 1
3. COLLECTOR 1
4. BASE 1
5. BASE 2
6. COLLECTOR 2

STYLE 10:
PIN 1. SOURCE 2
2. SOURCE 1
3. GATE 1
4. DRAIN 1
5. DRAIN 2
6. GATE 2

STYLE 11:
PIN 1. CATHODE 2
2. CATHODE 2
3. ANODE 1
4. CATHODE 1
5. CATHODE 1
6. ANODE 2

STYLE 12:
PIN 1. ANODE 2
2. ANODE 2
3. CATHODE 1
4. ANODE 1
5. ANODE 1
6. CATHODE 2

STYLE 13:
PIN 1. ANODE
2. N/C
3. COLLECTOR
4. EMITTER
5. BASE
6. CATHODE

STYLE 14:
PIN 1. VREF
2. GND
3. GND
4. IOUT
5. VEN
6. VCC

STYLE 15:
PIN 1. ANODE 1
2. ANODE 2
3. ANODE 3
4. CATHODE 3
5. CATHODE 2
6. CATHODE 1

STYLE 16:
PIN 1. BASE 1
2. EMITTER 2
3. COLLECTOR 2
4. BASE 2
5. EMITTER 1
6. COLLECTOR 1

STYLE 17:
PIN 1. BASE 1
2. EMITTER 1
3. COLLECTOR 2
4. BASE 2
5. EMITTER 2
6. COLLECTOR 1

STYLE 18:
PIN 1. VIN1
2. VCC
3. VOUT2
4. VIN2
5. GND
6. VOUT1

STYLE 19:
PIN 1. I OUT
2. GND
3. GND
4. V CC
5. V EN
6. V REF

STYLE 20:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR

STYLE 21:
PIN 1. ANODE 1
2. N/C
3. ANODE 2
4. CATHODE 2
5. N/C
6. CATHODE 1

STYLE 22:
PIN 1. D1 (i)
2. GND
3. D2 (i)
4. D2 (c)
5. VBUS
6. D1 (c)

STYLE 23:
PIN 1. Vn
2. CH1
3. Vp
4. N/C
5. CH2
6. N/C

STYLE 24:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE

STYLE 25:
PIN 1. BASE 1
2. CATHODE
3. COLLECTOR 2
4. BASE 2
5. EMITTER
6. COLLECTOR 1

STYLE 26:
PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

STYLE 27:
PIN 1. BASE 2
2. BASE 1
3. COLLECTOR 1
4. EMITTER 1
5. EMITTER 2
6. COLLECTOR 2

STYLE 28:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

STYLE 29:
PIN 1. ANODE
2. ANODE
3. COLLECTOR
4. EMITTER
5. BASE/ANODE
6. CATHODE

STYLE 30:
PIN 1. SOURCE 1
2. DRAIN 2
3. DRAIN 2
4. SOURCE 2
5. GATE 1
6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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DESCRIPTION:	**SC−88/SC70−6/SOT−363**	**PAGE 2 OF 2**

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Europe, Middle East and Africa Technical Support:
Phone: 00421 33 790 2910
For additional information, please contact your local Sales Representative

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